

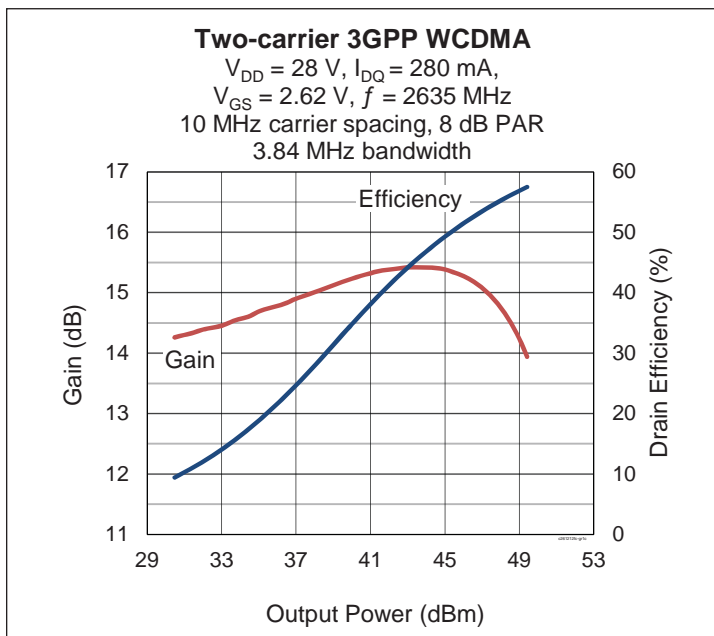
Thermally-Enhanced High Power RF LDMOS FET 120 W, 28 V, 2496 – 2690 MHz

Description

The PXAC261212FC is a 120-watt LDMOS FET with an asymmetric designed for use in multi-standard cellular power amplifier applications in the 2496 to 2690 MHz frequency band. It features dual-path design, input and output matching, and a thermally-enhanced package with earless flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PXAC261212FC
Package H-37248-4



Features

- Broadband internal matching
- Asymmetric design
 - Main $P_{1dB} = 50\text{ W}$
 - Peak $P_{1dB} = 75\text{ W}$
- CW performance in Doherty configuration, 2635 MHz, 28 V
 - Output power at $P_{1dB} = 107\text{ W}$
 - Gain = 14.4 dB
 - Efficiency = 57%
- Integrated ESD protection: Human Body Model, class 1C (per JESD22-A114)
- Capable of handling 10:1 VSWR @28 V, 120 W (CW) output power
- Low thermal resistance
- Pb-free and RoHS-compliant

RF Characteristics

Two-carrier WCDMA Specifications (tested in Infineon Doherty test fixture)

$V_{DD} = 28\text{ V}$, $V_{GS(peak)} = 1.3\text{ V}$, $I_{DQ} = 280\text{ mA}$, $P_{OUT} = 28\text{ W}$ average, $f_1 = 2630\text{ MHz}$, $f_2 = 2640\text{ MHz}$. 3GPP WCDMA signal: 3.84 MHz bandwidth, 8 dB PAR @0.01% CCDF.

Characteristic	Symbol	Min	Typ	Max	Unit
Linear Gain	G_{ps}	14.2	15.0	—	dB
Drain Efficiency	η_D	45	48	—	%
Intermodulation Distortion	IMD	—	-25	-22	dBc

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1.0	μA
	$V_{DS} = 63\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10.0	μA
Gate Leakage Current	$V_{GS} = 10\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1.0	μA
On-state Resistance	(main) $V_{GS} = 10\text{ V}, V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.19	—	Ω
	(peak) $V_{GS} = 10\text{ V}, V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.16	—	Ω
Operating Gate Voltage	(main) $V_{DS} = 28\text{ V}, I_{DQ} = 280\text{ mA}$	V_{GS}	2.1	2.6	3.1	V
	(peak) $V_{DS} = 28\text{ V}, I_{DQ} = 0\text{ A}$	V_{GS}	0.80	1.3	1.8	V

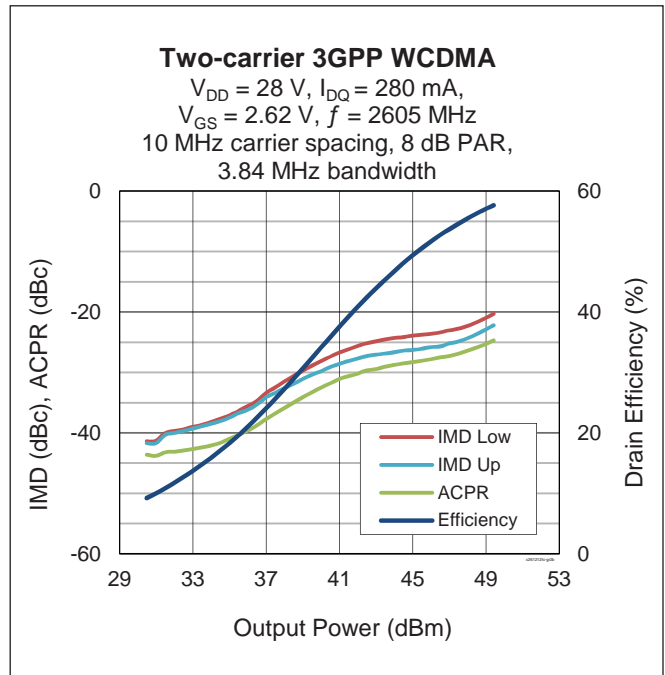
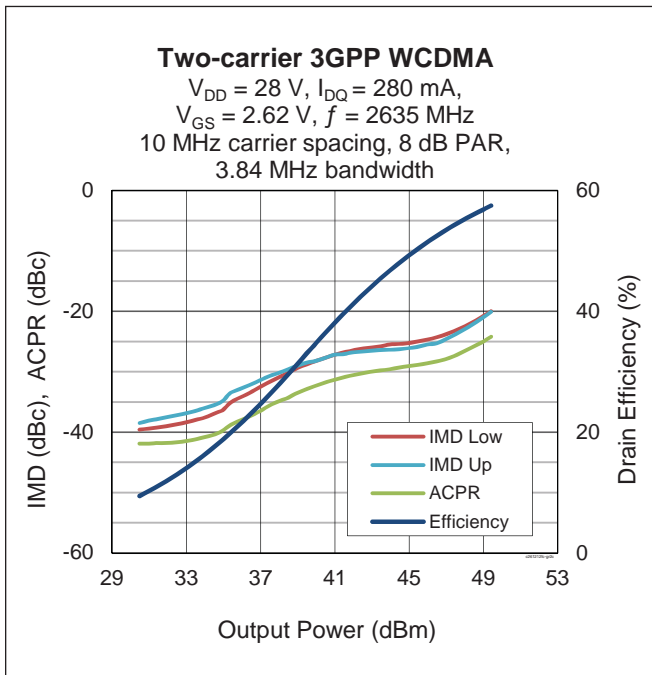
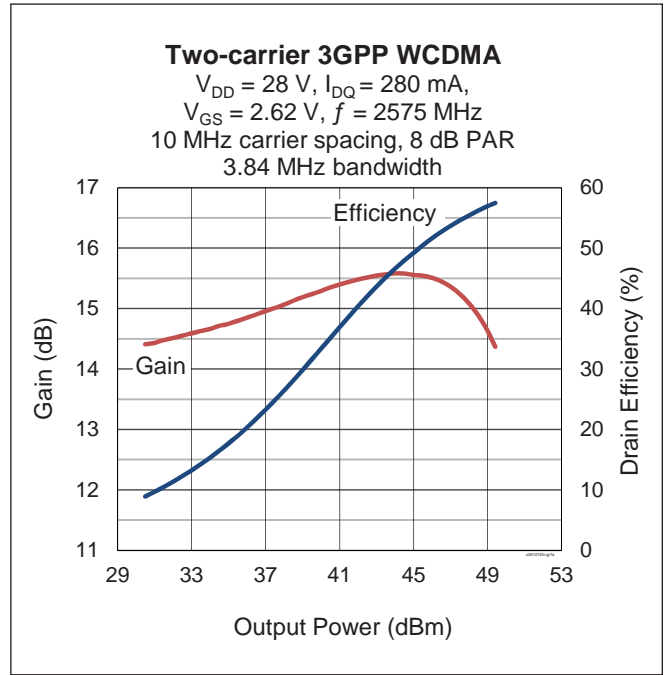
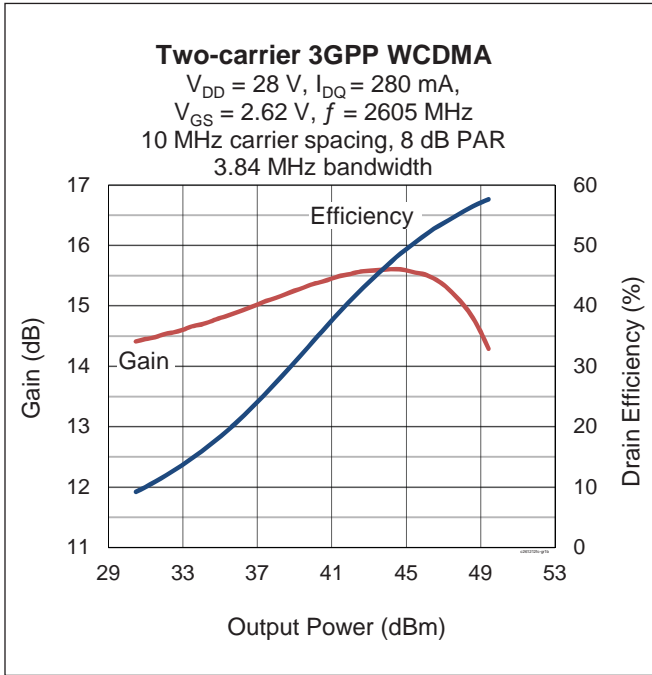
Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source Voltage	V_{DSS}	65	V
Gate-source Voltage	V_{GS}	-6 to +10	V
Operating Voltage	V_{DD}	0 to +32	V
Junction Temperature	T_J	225	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance ($T_{CASE} = 70^{\circ}\text{C}, 100\text{ W CW}$)	$R_{\theta JC}$	0.61	$^{\circ}\text{C/W}$

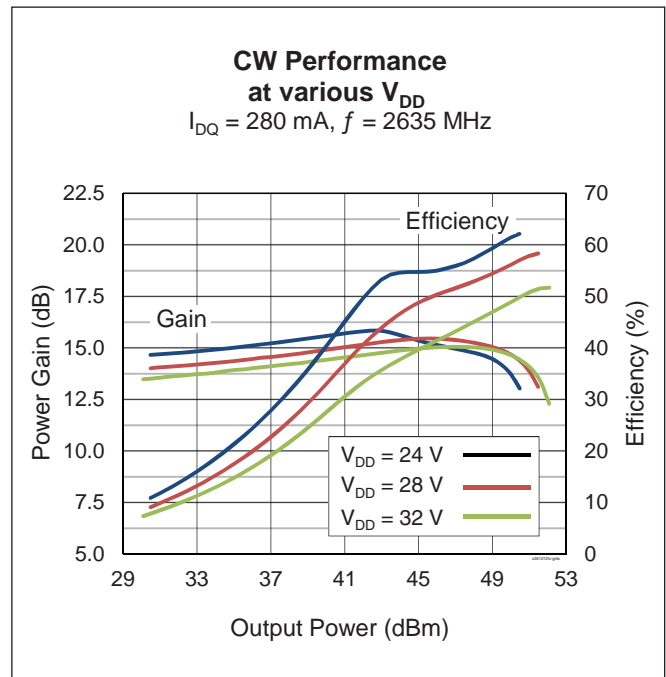
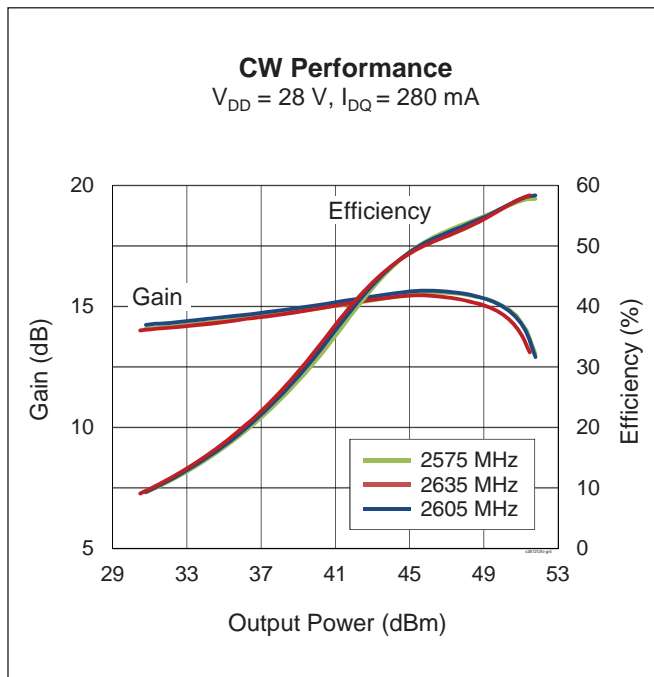
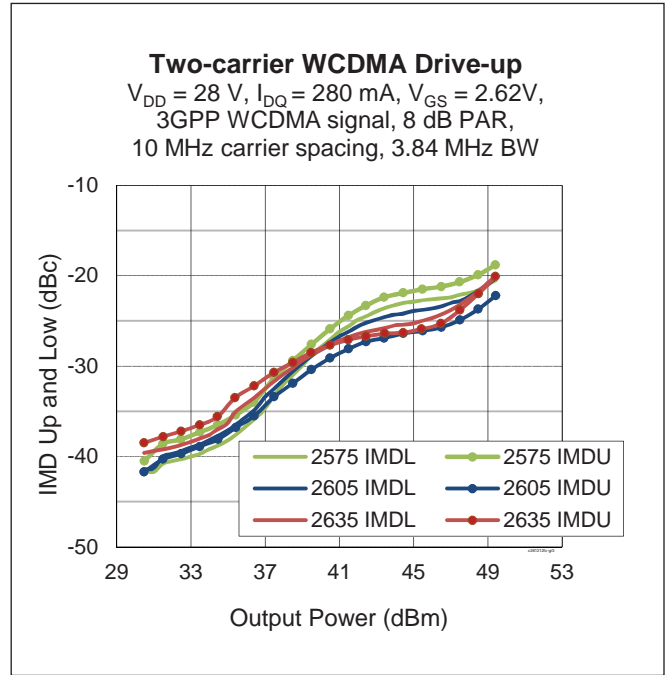
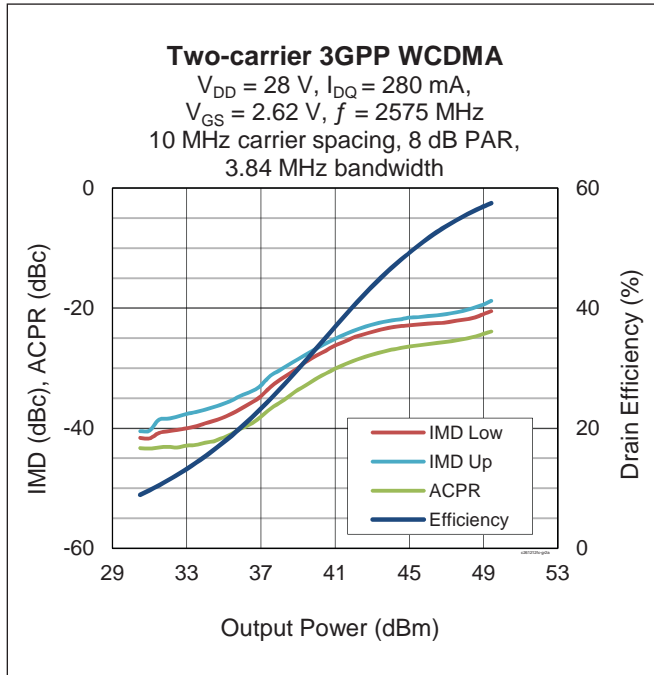
Ordering Information

Type and Version	Order Code	Package and Description	Shipping
PXAC261212FC V1	PXAC261212FCV1XWSA1	H-37248-4, ceramic open-cavity, earless	Tray
PXAC261212FC V1 R250	PXAC261212FCV1R250XTMA1	H-37248-4, ceramic open-cavity, earless	Tape & Reel, 250 pcs

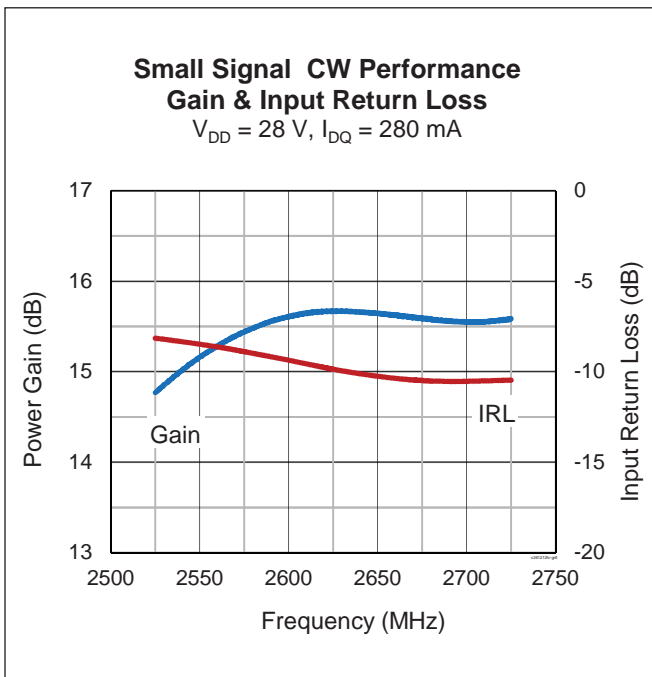
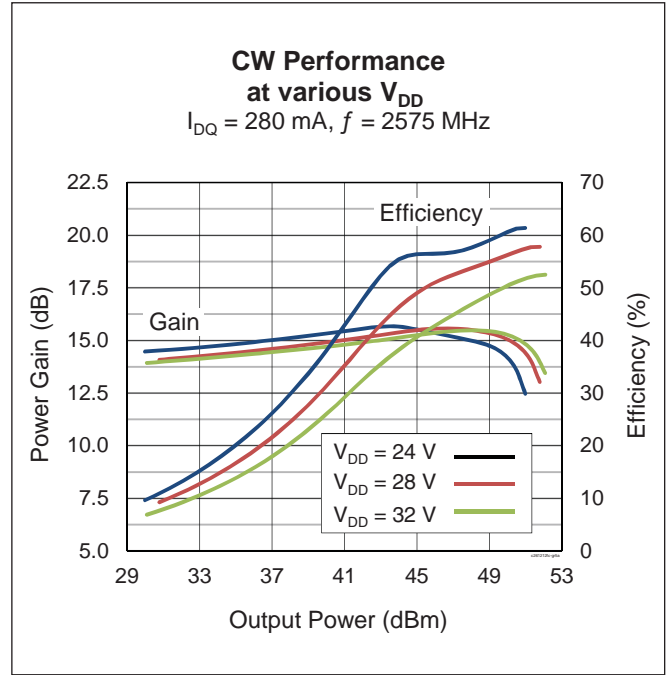
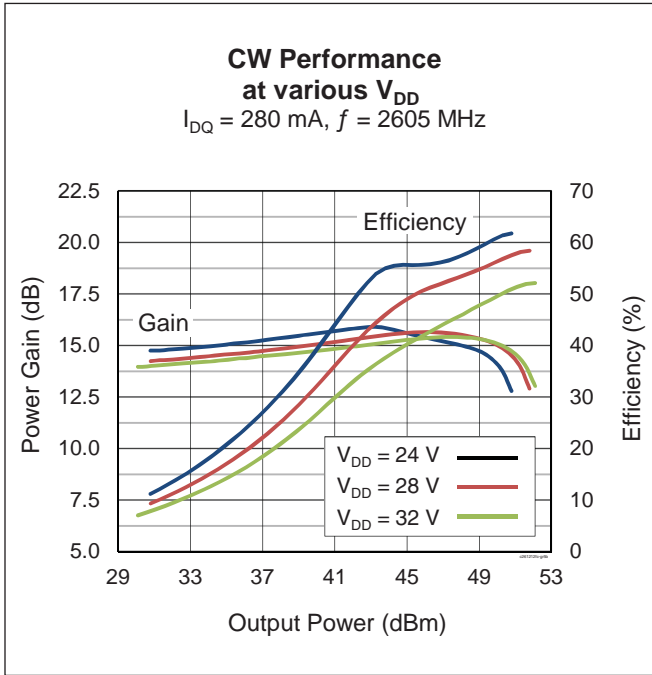
Typical Performance (data taken in Infineon Doherty reference test fixture)



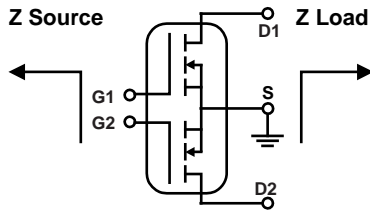
Typical Performance (cont.)



Typical Performance (cont.)



Load Pull Performance



Main side pulsed CW signal: 160 μ sec, 10% duty cycle; 28 V, $V_{GS} = 1.4$ V, $I_{DQ} = 250$ mA

Class AB		P_{1dB}										
		Max Output Power					Max PAE					
Freq [MHz]	Z_s [Ω]	Z_l [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]	Z_l [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]	
2490	5.1 – j14.5	2.8 – j5.8	16.9	48.53	71.3	52.8	6.0 – j4.2	19.1	46.90	49.0	62.4	
2590	6.8 – j16.6	2.8 – j6.2	17.0	48.30	67.6	50.4	5.5 – j3.6	19.4	46.68	46.6	61.1	
2690	12.9 – j17.8	2.9 – j6.0	17.2	48.30	67.6	50.4	4.5 – j3.3	19.5	46.76	47.4	60.4	

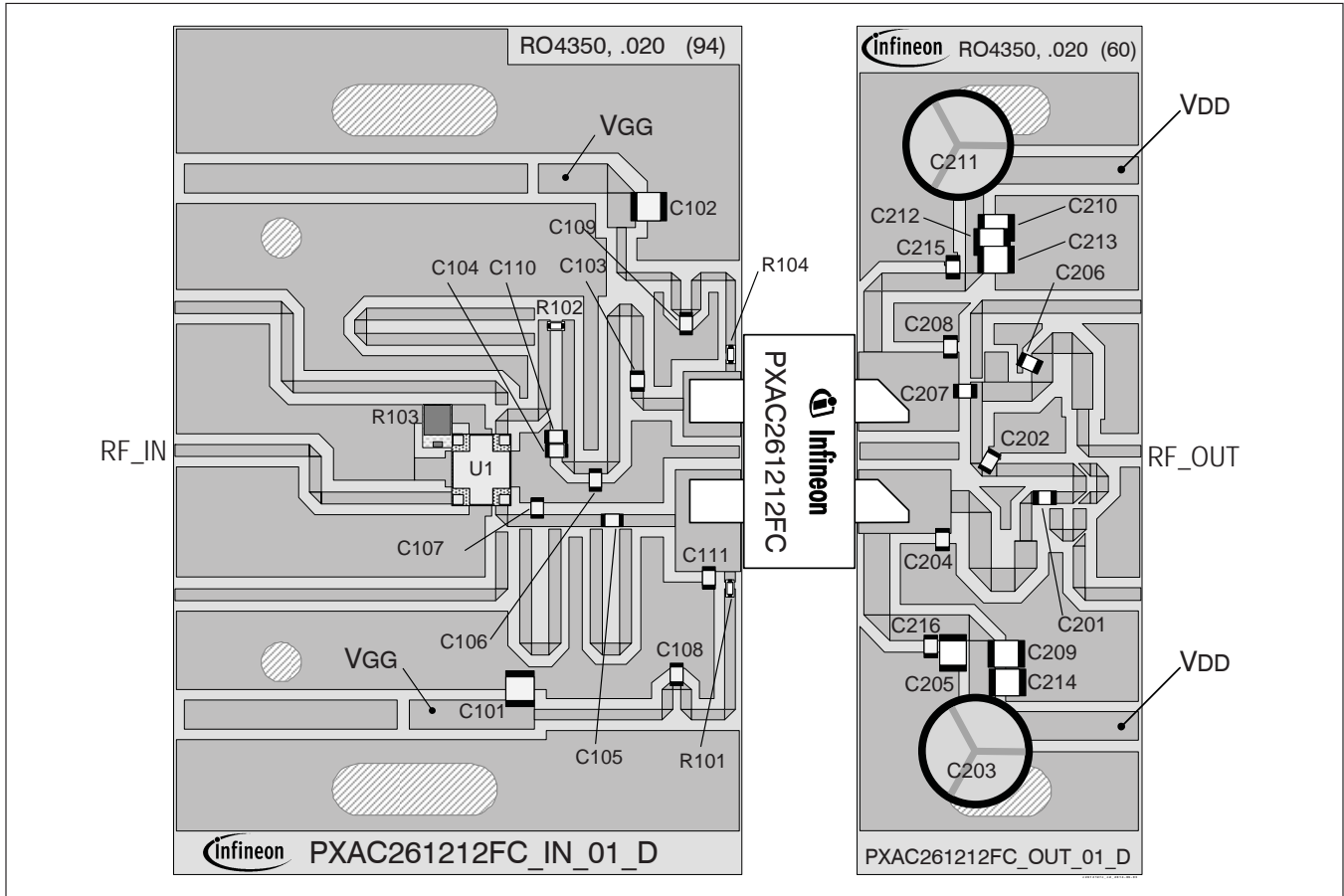
Peak side pulsed CW signal: 160 μ sec, 10% duty cycle; 28 V, $V_{GS} = 1.4$ V

Class C		P_{1dB}										
		Max Output Power					Max PAE					
Freq [MHz]	Z_s [Ω]	Z_l [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]	Z_l [Ω]	Gain [dB]	P_{OUT} [dBm]	P_{OUT} [W]	PAE [%]	
2490	4.5 – j11.4	11.2 – j7.5	13.0	50.27	106.4	55.6	4.3 – j5.4	14.1	48.40	69.2	65.3	
2590	4.7 – j12.9	13.1 – j6.3	13.4	50.08	101.9	54.1	6.0 – j6.3	14.6	48.60	72.4	63.2	
2690	9.2 – j14.5	14.1 – j3.4	13.7	50.03	100.7	55.5	8.0 – j7.0	14.7	48.70	74.1	62.0	

Reference Circuit, tuned for 2575 – 2675 MHz

DUT	PXAC261212FC
Test Fixture Part No.	LTA/PXAC261212FC V1
PCB	Rogers 4350, 0.508 mm [.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$
Find Gerber files for this reference fixture on the Infineon Web site at (www.infineon.com/rfpower)	

Reference Circuit (cont.)



Reference circuit assembly diagram (not to scale)

Assembly Information

Component	Description	Manufacturer	P/N
Input			
C101, C102	Chip capacitor, 4.7 μ F	Murata Electronics North America	GRM32ER71H475KA88L
C103, C105, C108, C109	Chip capacitor, 10 pF	ATC	ATC600F100JW250T
C104	Chip capacitor, 0.4 pF	ATC	ATC600F0R4CW250T
C106, C107	Chip capacitor, 0.8 pF	ATC	ATC600F0R8AW250T
C110	Chip capacitor, 0.2 pF	ATC	ATC600F0R2AW250T
C111	Chip capacitor, 0.3 pF	ATC	ATC600F0R3CW250T
R101, R104	Resistor, 10 Ohm	Panasonic – ECG	ERJ-3GEYJ100V
R102	Resistor, 5.1k Ohm	Panasonic – ECG	ERJ-3GEYJ512V
R103	Resistor, 50 Ohm	Anaren	RFP-060120A15Z50
U1	90° RF hybrid coupler	Anaren	XC2650P-03S

(table continued next page)

Reference Circuit (cont.)

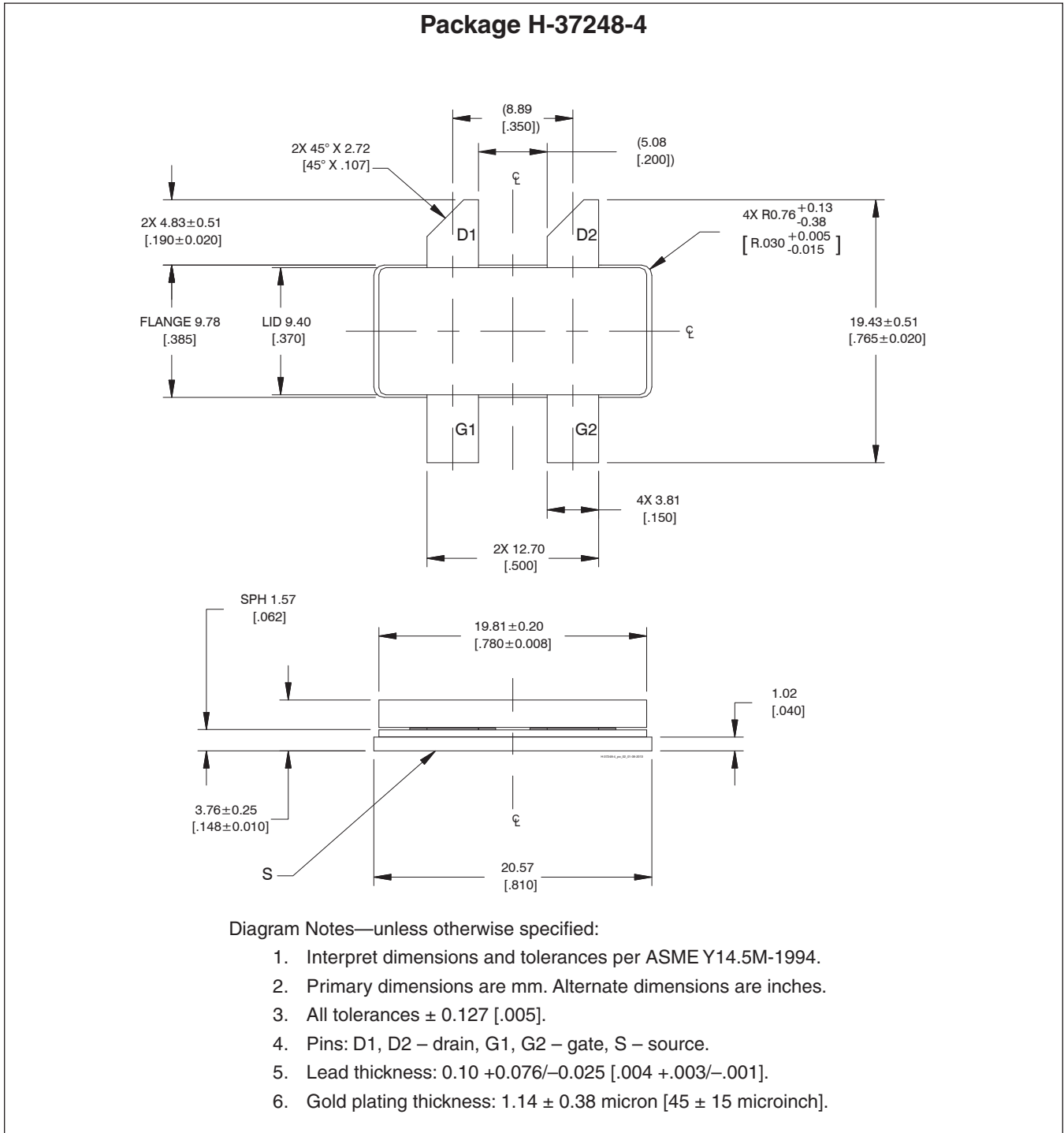
Assembly Information (cont.)

Component	Description	Manufacturer	P/N
Output			
C201, C215, C216	Chip capacitor, 10 pF	ATC	ATC600F100JW250T
C202, C204, C211, C208	Chip capacitor, 0.5 pF	ATC	ATC600F0R5CW250T
C203	Capacitor, 220 μ F	Cornell Dubilier Electronics (CDE)	SK221M050ST
C205, C209, C210, C212, C213, C214	Chip capacitor, 4.7 μ F	Murata Electronics North America	GRM32ER71H475KA88L
C206	Chip capacitor, 0.3 pF	ATC	ATC600F0R3CW250T
C207	Chip capacitor, 3.9 pF	ATC	ATC600F3R9CW250T

Pinout Diagram (top view)



Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page (www.infineon.com/rfpower)

Revision History

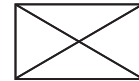
Revision	Date	Data Sheet	Page	Subjects (major changes since last revision)
01	2014-03-03	Advance	all	Proposed specification for new product development.
02	2014-06-12	Production	all	Specification for production-released device.
02.1	2014-06-30	Production	1	Corrected typo in features.

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highpowerRF@infineon.com

To request other information, contact us at:
 +1 877 465 3667 (1-877-GO-LDMOS) USA
 or +1 408 776 0600 International



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